



APPENDIX

Changes to Claims:

Claims 25-27 are added.

The following is a marked-up version of the amended claim(s) 1-24:

1. (Amended) A pyrolytic boron nitride double container for a source of molecular beams used in molecular beam epitaxy, comprising:
an outer container having an outer container transmissivity with respect to light having a wave number of 2600 cm⁻¹ to 6500 cm⁻¹, and
an inner container having an inner container transmissivity with respect to light having a wave number of 2600 cm⁻¹ to 6500 cm⁻¹;
wherein said inner container transmissivity is 90% or less of said outer container transmissivity~~the transmissivity of an inner container of the pyrolytic boron nitride double container with respect to light having a wave number of 2600 cm⁻¹ to 6500 cm⁻¹ is 90% or less of that of an outer container.~~
2. (Amended) The pyrolytic boron nitride double container according to Claim 1, said inner container comprising an inner surface and an outer surface;
wherein the said outer surface has a roughness of the outer surface of the inner container is roughened so such that said inner container transmissivity is 90% or less of said outer container transmissivity~~the transmissivity of the inner container is 90% or less of that of the outer container.~~
3. (Amended) The pyrolytic boron nitride double container according to Claim 1, comprising a doped layer comprising~~wherein an at least one element except nitrogen and boron is doped into the said inner container to form a doped layer;~~
wherein said at least one element is not selected from the group consisting of nitrogen and boron, and

~~wherein said doped layer has~~ while at least one of the a thickness, an area, and
a doping density of the doped layer is adjusted, so such that said inner container transmissivity
is 90% or less of said outer container transmissivity ~~the transmissivity of the inner container~~
~~is 90% or less of that of the outer container.~~

4. (Amended) The pyrolytic boron nitride double container according to
Claim 2, comprising a doped layer comprising wherein an at least one element except nitrogen
and boron is doped into the said inner container to form a doped layer;

wherein said at least one element is not selected from the group consisting of
nitrogen and boron, and

~~while~~ wherein said doped layer has at least one of the a thickness, an area, and
a doping density of the doped layer is adjusted, so such that said inner container
transmissivity is 90% or less of said outer container transmissivity ~~the transmissivity of the~~
~~inner container is 90% or less of that of the outer container.~~

5. (Amended) The pyrolytic boron nitride double container according to
Claim 3, wherein ~~the said~~ doped layer is located within the inner container, and wherein said
doped layer is formed such that the layer is not located ~~exposed on neither said inner surface~~
~~nor said outer surface of the said inner container.~~

6. (Amended) The pyrolytic boron nitride double container according to
Claim 4, wherein ~~the said~~ doped layer is located within the inner container, and wherein said
doped layer is formed such that the layer is exposed ~~not located on neither said inner surface~~
~~nor on said outer surface of the said inner container.~~

7. (Amended) The pyrolytic boron nitride double container according to
Claim 3, wherein ~~pyrolytic boron nitride is doped with one or more elements~~ said at least one
element is selected from the group consisting of Si, C, and Al.

8. (Amended) The pyrolytic boron nitride double container according to Claim 4, wherein ~~said at least one element is pyrolytic boron nitride is doped with one or more elements~~ selected from the group consisting of Si, C, and Al.

9. (Amended) The pyrolytic boron nitride double container according to Claim 5, wherein ~~said at least one element is pyrolytic boron nitride is doped with one or more elements~~ selected from the group consisting of Si, C, and Al.

10. (Amended) The pyrolytic boron nitride double container according to Claim 6, wherein ~~said at least one element is pyrolytic boron nitride is doped with one or more elements~~ selected from the group consisting of Si, C, and Al.

11. (Amended) The pyrolytic boron nitride double container according to Claim 1, wherein ~~the an inner container~~ thickness of ~~the said~~ inner container is ~~increased greater than an outer container thickness of said outer container so such that said inner container transmissivity is 90% or less of said outer container transmissivity. the transmissivity of the inner container is 90% or less of that of the outer container.~~

12. (Amended) The pyrolytic boron nitride double container according to Claim 2, wherein ~~the an inner container~~ thickness of ~~the said~~ inner container is ~~increased greater than an outer container thickness of said outer container so such that said inner container transmissivity is 90% or less of said outer container transmissivity. the transmissivity of the inner container is 90% or less of that of the outer container.~~

13. (Amended) The pyrolytic boron nitride double container according to Claim 1, wherein said inner container comprises a top, open portion and a bottom portion, and wherein the said inner container transmissivity of the inner container has a profile such that the transmissivity changes varies in the height direction of the inner container from said bottom portion to said top, open portion.

14. (Amended) The pyrolytic boron nitride double container according to Claim 2, wherein said inner container comprises a top, open portion and a bottom portion, and wherein said inner container ~~the transmissivity varies of the inner container has a profile~~ such that the transmissivity changes in the height direction of the inner container from said bottom portion to said top, open portion.

15. (Amended) The pyrolytic boron nitride double container according to Claim 13, wherein said inner container ~~the transmissivity of the inner container~~ decreases at the opening portion of the inner container from said bottom portion to said top, open portion.

16. (Amended) The pyrolytic boron nitride double container according to Claim 14, wherein ~~the~~ said inner container ~~transmissivity of the inner container~~ decreases at the opening portion of the inner container from said bottom portion to said top, open portion.

17. (Amended) The pyrolytic boron nitride double container according to Claim 13, wherein ~~the~~ said inner container ~~transmissivity of the inner container~~ increases from said bottom portion to said top, open portion ~~at the opening portion of the inner container.~~

18. (Amended) The pyrolytic boron nitride double container according to Claim 14, wherein ~~the~~ said inner container ~~transmissivity of the inner container~~ increases from said bottom portion to said top, open portion ~~at the opening portion of the inner container.~~

19. (Amended) The pyrolytic boron nitride double container according to Claim 1, ~~wherein there is~~ comprising a gap between ~~the~~ said inner container and ~~the~~ said outer container.

20. (Amended) The pyrolytic boron nitride double container according to Claim 2, ~~wherein there is~~ comprising a gap between ~~the~~ said inner container and ~~the~~ said outer container.

21. (Amended) The pyrolytic boron nitride double container according to Claim 19, wherein ~~the said gap between the inner container and the outer container~~ is 0.2 to 30 mm.

22. (Amended) The pyrolytic boron nitride double container according to Claim 20, wherein ~~the said gap between the inner container and the outer container~~ is 0.2 to 30 mm.

23. (Amended) A method of manufacturing a pyrolytic boron nitride double container for a source of molecular beams used in molecular beam epitaxy, comprising:
~~_____ wherein forming an inner container and an outer container of the pyrolytic boron nitride double container are formed by a CVD reaction,~~
~~_____ roughening the an outer surface of the formed inner container is roughened to,~~
thereby adjusting ~~the an~~ amount of light scattered at the outer surface, and
~~_____ settingsuch that the an inner container transmissivity of the inner container~~
with respect to light having a wave number of 2600 cm^{-1} to 6500 cm^{-1} ~~is set to 90% or less of~~
~~that of the an~~ outer container transmissivity, with respect to light having a wave number of
 2600 cm^{-1} to 6500 cm^{-1} .

24. (Amended) A method of manufacturing a pyrolytic boron nitride double container for a source of molecular beams used in molecular beam epitaxy, comprising:
~~_____ depositingin which pyrolytic boron nitride is deposited on a graphite mandrel~~
by a CVD reaction, thereby in order to forming the double container,
~~_____ and the double container is then separated from the mandrel, wherein forming~~
a doped layer in the pyrolytic boron nitride container by introducing a dopant gas is
~~introduced during the CVD reaction of the inner container in order to form a doped layer in~~
~~the pyrolytic boron nitride container,~~

_____ adjusting ~~and~~ at least one of the thickness, area and the doping density of the doped layer ~~is adjusted so as to,~~

_____ setting the inner container transmissivity ~~of the inner container~~ with respect to light having a wave number of 2600 cm^{-1} to 6500 cm^{-1} to 90% or less of ~~that of the~~ an outer container transmissivity, with respect to light having a wave number of 2600 cm^{-1} to 6500 cm^{-1} , and

_____ separating the double container from the mandrel.